ELSEVIER

Journal of Non-Crystalline Solids 190 (1995) 301–303

JOURNAL OF NON-CRYSTALLINE SOLIDS

Author index

Abe, Y., see Hosono, H. 190 (1995) 185
Achibat, T., see Duval, E. 190 (1995) 258
Adriaenssens, G.J., see Baranovskii, S.D. 190 (1995) 117
Adriaenssens, G.J., see Baranovskii, S.D. 190 (1995) 283
Adriaenssens, G.J., see Yan, B. 190 (1995) 85
Algar, C.D., see Rigden, J.S. 190 (1995) 276
Aristov, Yu.I., see Jarzębski, A.B. 190 (1995) 198
Auzel, F., see Santa-Cruz, P. 190 (1995) 238

Baranovskii, S.D., F. Hensel, K. Ruckes, P. Thomas and G.J. Adriaenssens, Potential fluctuations in amorphous silicon 190 (1995) 117
Baranovskii, S.D., P. Thomas and G.J. Adriaenssens, The concept of transport energy and its application to steady-state photoconductivity in amorphous silicon 190 (1995) 283
Bässler, H., see Hartenstein, B. 190 (1995) 112
Boukenter, A., see Duval, E. 190 (1995) 258
Branz, H.M., see Fedders, P.A. 190 (1995) 142
Brinker, C.J., see Prakash, S.S. 190 (1995) 264
Byun, J.-O., B.-H. Kim, K.-S. Hong, H.-J. Jung, S.-W. Lee and A.A. Izyneev, Properties and structure of $RO–Na_2O–Al_2O_3–P_2O_5$ (R = Mg, Ca, Sr, Ba) glasses 190 (1995) 288

Calemczuk, R., see Duval, E. 190 (1995) 258
Carlen, M.W., see Crandall, R.S. 190 (1995) 133
Chen, I.-S. and C.R. Wronski, Internal photoemission on a-Si:H Schottky barrier structures revisited 190 (1995) 58
Cho, J. and S.W. Martin, Density measurements of $xK_2S + (1-x)B_2S_3$ $(0 \leqslant x \leqslant 0.75)$ glasses: correlation with short range order 190 (1995) 244
Cohen, J.D. and F. Zhong, Transient modulated photocurrent studies in hydrogenated amorphous silicon: a new look at defect relaxation dynamics 190 (1995) 123
Crandall, R.S. and M.W. Carlen, Connection between dangling-bond relaxation and metastability in p-type hydrogenated amorphous silicon 190 (1995) 133

Dexpert-Ghys, J., see Santa-Cruz, P. 190 (1995) 238
Duval, E., T. Achibat, A. Boukenter, B. Varrel, R. Calemczuk and B. Salce, Low-energy excitations in polyvinyl chloride: Raman scattering and thermal properties 190 (1995) 258

Eliat, A., see Yan, B. 190 (1995) 85
Equer, B. and A. Ilie, High electric field forming of a-Si:H p–i–n diodes 190 (1995) 67

Fedders, P.A. and H.M. Branz, Structural memory and defect relaxation 190 (1995) 142
Fritzsche, H., The structure of light-induced metastable defects in a-Si:H 190 (1995) 180
Fuhs, W., see Ulber, I. 190 (1995) 9

Glas, F., see Santa-Cruz, P. 190 (1995) 238
Gleskova, H. and S. Wagner, Are both thermal and light-induced annealing of metastable defects in a-Si:H driven by electrons? 190 (1995) 157

Han, D. and K. Wang, Electroluminescence from hydrogenated amorphous silicon p–i–n diodes 190 (1995) 74
Han, D., see Vanderhaghen, R. 190 (1995) 95
Han, D., see Yan, B. 190 (1995) 85
Hartenstein, B. and H. Bässler, Transport energy for hopping in a Gaussian density of states distribution 190 (1995) 112
Hensel, F., see Baranovskii, S.D. 190 (1995) 117
Herzog, K., B. Thomas, D. Sprenger and C. Jäger, REDOR NMR: approaching structural elucidation of hydrated layers in silicate electrode glasses 190 (1995) 296
Hikita, H., see Morigaki, K. 190 (1995) 38
Hong, K.-S., see Byun, J.-O. 190 (1995) 288
Hosono, H. and Y. Abe, Porous glass-ceramics composed of a titanium phosphate crystal skeleton: A review 190 (1995) 185
Hurd, A.J., see Prakash, S.S. 190 (1995) 264

Ibrahim, F., see Rigden, J.S. 190 (1995) 276
Ilie, A., see Equer, B. 190 (1995) 67
Izyneev, A.A., see Byun, J.-O. 190 (1995) 288

Jacquin, J.R. and M. Tomozawa, Crystallization of lithium metasilicate from lithium disilicate glass 190 (1995) 233
Jäger, C., see Herzog, K. 190 (1995) 296
Jarzębski, A.B., J. Lorenc, Yu.I. Aristov and N. Lisitza, Porous texture characteristics of a homologous series of base-catalyzed silica aerogels 190 (1995) 198
Jing, Z., see Lucovsky, G. 190 (1995) 169
Jung, H.-J., see Byun, J.-O. 190 (1995) 288

Kemp, M., A new model of low-temperature photoluminescence in amorphous semiconductors 190 (1995) 21
Kim, B.-H., see Byun, J.-O. 190 (1995) 288
Kondo, M., see Morigaki, K. 190 (1995) 38

Lee, S.-W., see Byun, J.-O. 190 (1995) 288
Lisitza, N., see Jarzębski, A.B. 190 (1995) 198
Lorenc, J., see Jarzębski, A.B. 190 (1995) 198
Lu, Z., see Lucovsky, G. 190 (1995) 169
Lucovsky, G., P. Santos-Filho, Z. Lu, Z. Jing and J.L. Whitten, Bonding of oxygen and nitrogen atoms in hydrogenated amorphous silicon alloys 190 (1995) 169

Mahan, A.H., see Vaněček, M. 190 (1995) 163
Mao, D. and P.C. Taylor, Optically detected ESR studies of recombination processes in a-Si : H 190 (1995) 48
Martin, S.W., see Cho, J. 190 (1995) 244
Masson, D.P., A. Ouhlal and A. Yelon, Long-range structural relaxation in the Staebler–Wronski effect 190 (1995) 151
Matsuyama, I., see Satoh, S. 190 (1995) 206
McCormick, A.V., see Pozarnsky, G.A. 190 (1995) 212
Mell, H., see Ulber, I. 190 (1995) 9
Morigaki, K., H. Hikita and M. Kondo, Self-trapping of holes and related phenomena in a-Si : H 190 (1995) 38
Morin, D., see Santa-Cruz, P. 190 (1995) 238

Newport, R.J., see Rigden, J.S. 190 (1995) 276
Nickel, N.H., see Street, R.A. 190 (1995) 33
North, A.N., see Rigden, J.S. 190 (1995) 276

Ookawa, M., see Shibata, M. 190 (1995) 226
Ouhlal, A., see Masson, D.P. 190 (1995) 151

Pozarnsky, G.A. and A.V. McCormick, Multinuclear NMR study of aluminosilicate sol–gel synthesis using the prehydrolysis method 190 (1995) 212
Prakash, S.S., C.J. Brinker and A.J. Hurd, Silica aerogel films at ambient pressure 190 (1995) 264

Rigden, J.S., C.D. Algar, R.J. Newport, A.N. North, F. Ibrahim and J.I.B. Wilson, Small-angle X-ray scattering studies of a-Si : C : H 190 (1995) 276
Ruckes, K., see Baranovskii, S.D. 190 (1995) 117

Sadoc, A., see Santa-Cruz, P. 190 (1995) 238
Salce, B., see Duval, E. 190 (1995) 258
Saleh, R., see Ulber, I. 190 (1995) 9
Santa-Cruz, P., D. Morin, J. Dexpert-Ghys, A. Sadoc, F. Glas and F. Auzel, New lanthanide-doped fluoride-based vitreous materials for laser applications 190 (1995) 238
Santos-Filho, P., see Lucovsky, G. 190 (1995) 169
Satoh, S., I. Matsuyama and K. Susa, Diffusion of gases in porous silica gel 190 (1995) 206
Schiff, E.A., Diffusion-controlled bimolecular recombination of electrons and holes in a-Si : H 190 (1995) 1
Shibata, M., M. Ookawa and T. Yokokawa, Studies of NiO dissolved in alkali silicate melts based on redox potential and visible absorption spectra 190 (1995) 226
Solomon, I., Very long relaxation times of conductivity in a-Si : H and its alloys 190 (1995) 107
Sprenger, D., see Herzog, K. 190 (1995) 296
Street, R.A., N.H. Nickel and C.C. Tsai, Luminescence of a-Si : C : H alloys deposited with hydrogen dilution 190 (1995) 33
Susa, K., see Satoh, S. 190 (1995) 206

Taylor, P.C., see Mao, D. 190 (1995) 48
Thomas, B., see Herzog, K. 190 (1995) 296
Thomas, P., see Baranovskii, S.D. 190 (1995) 117
Thomas, P., see Baranovskii, S.D. 190 (1995) 283
Tomozawa, M., see Jacquin, J.R. 190 (1995) 233
Tsai, C.C., see Street, R.A. 190 (1995) 33

Ulber, I., R. Saleh, W. Fuhs and H. Mell, Recombination at defects in amorphous silicon (a-Si : H) 190 (1995) 9

Vanderhaghen, R. and D. Han, Interface effects on double injection current and photocurrent in a-Si : H n–i–p and p–i–n diodes 190 (1995) 95
Vaněček, M. and A.H. Mahan, Thermally induced metastable defect studies on hydrogenated amorphous silicon films with different hydrogen contents 190 (1995) 163
Varrel, B., see Duval, E. 190 (1995) 258

Wagner, S., see Gleskova, H. 190 (1995) 157
Wang, K., see Han, D. 190 (1995) 74
Whitten, J.L., see Lucovsky, G. 190 (1995) 169
Wilson, J.I.B., see Rigden, J.S. 190 (1995) 276
Wronski, C.R., see Chen, I.-S. 190 (1995) 58

Yan, B., G.J. Adriaenssens, A. Eliat and D. Han, Forward current transients in amorphous silicon p–i–n structures 190 (1995) 85
Yelon, A., see Masson, D.P. 190 (1995) 151
Yokokawa, T., see Shibata, M. 190 (1995) 226
Zahra, A.-M., see Zahra, C.Y. 190 (1995) 251
Zahra, C.Y. and A.-M. Zahra, Calorimetric studies of AgI-doped tellurite glasses 190 (1995) 251
Zhong, F., see Cohen, J.D. 190 (1995) 123

ELSEVIER

Journal of Non-Crystalline Solids 190 (1995) 304–306

JOURNAL OF NON-CRYSTALLINE SOLIDS

Subject index

Aerogels
Processing Variables, Structural Relaxation 190 (1995) 264

Alkali Borate Glasses
Borates, Density 190 (1995) 244

Alkali Silicate Glasses
Crystallization, Nitridation 190 (1995) 233
Gels, Liquids, Optical Properties 190 (1995) 226

Alloys
Bonding, Hydrogenation 190 (1995) 169
Conductivity, Hydrogenation, Silicon, Thin Films 190 (1995) 107
Hydrogen Effects, Luminescence 190 (1995) 33

Amorphous Carbon
Secondary Electron Emission, Small Angle X-ray Scattering 190 (1995) 276

Amorphous Semiconductors
Electronic Structure, Modelling, Transport Properties – Solids 190 (1995) 283

Annealing Effects
Defects, Hydrogenation, Thin Films 190 (1995) 163
Hydrogenation, Photoinduced Effects, Silicon, Thermal Properties 190 (1995) 157

Bonding
Alloys, Hydrogenation 190 (1995) 169

Borates
Alkali Borate Glasses, Density 190 (1995) 244

Conductivity
Alloys, Hydrogenation, Silicon, Thin Films 190 (1995) 107

Crystallization
Alkali Silicate Glasses, Nitridation 190 (1995) 233
Fluorescence Spectra, Fluorides, Lasers 190 (1995) 238

Dangling Bonds
Hydrogenation, Metastability, Relaxation 190 (1995) 133

Defects
Annealing Effects, Hydrogenation, Thin Films 190 (1995) 163
Electron Spin Resonance, Optical Properties, Photo-emission, Recombination 190 (1995) 9
Excitons 190 (1995) 38
Photoconductivity, Relaxation, Transient Effects 190 (1995) 123
Structural Relaxation, Transient Effects 190 (1995) 142

Density
Alkali Borate Glasses, Borates 190 (1995) 244

Deposition Techniques
Diodes, Electrical Properties 190 (1995) 67

Devices
Electronic Conductivity, Relaxation 190 (1995) 85

Diffusion
Electron Interactions, Modelling 190 (1995) 1
Gels, Sol–Gel Processes 190 (1995) 206

Diodes
Deposition Techniques, Electrical Properties 190 (1995) 67
Electroluminescence, Hydrogenation 190 (1995) 74
Interfaces, Photoconductivity 190 (1995) 95

Electrical Properties
Deposition Techniques, Diodes 190 (1995) 67

Electroluminescence
Diodes, Hydrogenation 190 (1995) 74

Electron Interactions
Diffusion, Modelling 190 (1995) 1

Electron Spin Resonance
Defects, Optical Properties, Photo-emission, Recombination 190 (1995) 9
Optical Properties, Recombination 190 (1995) 48

Electronic Conductivity
Devices, Relaxation 190 (1995) 85
Hydrogen Effects, Silicon 190 (1995) 117

Electronic Structure
Amorphous Semiconductors, Modelling, Transport Properties – Solids 190 (1995) 283

Excitons
Defects 190 (1995) 38

Fluorescence Spectra
Crystallization, Fluorides, Lasers 190 (1995) 238

Fluorides
Crystallization, Fluorescence Spectra, Lasers 190 (1995) 238

Gels
Alkali Silicate Glasses, Liquids, Optical Properties 190 (1995) 226
Diffusion, Sol–Gel Processes 190 (1995) 206
Porosity 190 (1995) 198

Glass Ceramics
Porosity, Structure 190 (1995) 185

Halide Glasses
Oxides, Thermal Properties 190 (1995) 251

Hopping
Theory 190 (1995) 112

Hydrogen Effects
Alloys, Luminescence 190 (1995) 33
Electronic Conductivity, Silicon 190 (1995) 117

Hydrogen in Glass
Photoinduced Effects, Silica 190 (1995) 180

Hydrogenation
Alloys, Bonding 190 (1995) 169
Alloys, Conductivity, Silicon, Thin Films 190 (1995) 107
Annealing Effects, Defects, Thin Films 190 (1995) 163
Annealing Effects, Photoinduced Effects, Silicon, Thermal Properties 190 (1995) 157
Dangling Bonds, Metastability, Relaxation 190 (1995) 133
Diodes, Electroluminescence 190 (1995) 74

Infra-red Absorption
Phosphates, Structure 190 (1995) 288

Interfaces
Diodes, Photoconductivity 190 (1995) 95

Lasers
Crystallization, Fluorescence Spectra, Fluorides 190 (1995) 238

Liquids
Alkali Silicate Glasses, Gels, Optical Properties 190 (1995) 226

Luminescence
Alloys, Hydrogen Effects 190 (1995) 33

Metastability
Dangling Bonds, Hydrogenation, Relaxation 190 (1995) 133

Mobility
Mobility Edge, Photo-emission 190 (1995) 58

Mobility Edge
Mobility, Photo-emission 190 (1995) 58

Modelling
Amorphous Semiconductors, Electronic Structure, Transport Properties – Solids 190 (1995) 283
Diffusion, Electron Interactions 190 (1995) 1
Photo-emission, Semiconductors 190 (1995) 21

Nitridation
Alkali Silicate Glasses, Crystallization 190 (1995) 233

Nuclear Magnetic Resonance
Oxides, Sol–Gel Processes 190 (1995) 212
Silicates, Structure 190 (1995) 296

Optical Properties
Alkali Silicate Glasses, Gels, Liquids 190 (1995) 226
Defects, Electron Spin Resonance, Photo-emission, Recombination 190 (1995) 9
Electron Spin Resonance, Recombination 190 (1995) 48

Oxides
Halide Glasses, Thermal Properties 190 (1995) 251
Nuclear Magnetic Resonance, Sol–Gel Processes 190 (1995) 212

Phosphates
Infra-red Absorption, Structure 190 (1995) 288

Photoconductivity
Defects, Relaxation, Transient Effects 190 (1995) 123
Diodes, Interfaces 190 (1995) 95

Photo-emission
Defects, Electron Spin Resonance, Optical Properties, Recombination 190 (1995) 9
Mobility, Mobility Edge 190 (1995) 58
Modelling, Semiconductors 190 (1995) 21

Photoinduced Effects
Annealing Effects, Hydrogenation, Silicon, Thermal Properties 190 (1995) 157
Hydrogen in Glass, Silica 190 (1995) 180

Polymers
Raman Spectra, Thermal Properties, Tunneling 190 (1995) 258

Porosity
Gels 190 (1995) 198
Glass Ceramics, Structure 190 (1995) 185

Processing Variables
Aerogels, Structural Relaxation 190 (1995) 264

Raman Spectra
Polymers, Thermal Properties, Tunneling 190 (1995) 258

Recombination
Defects, Electron Spin Resonance, Optical Properties, Photo-emission 190 (1995) 9
Electron Spin Resonance, Optical Properties 190 (1995) 48

Relaxation
Dangling Bonds, Hydrogenation, Metastability 190 (1995) 133
Defects, Photoconductivity, Transient Effects 190 (1995) 123
Devices, Electronic Conductivity 190 (1995) 85
Stäbler–Wronski Effect, Structure 190 (1995) 151

Secondary Electron Emission
Amorphous Carbon, Small Angle X-ray Scattering 190 (1995) 276

Semiconductors
Modelling, Photo-emission 190 (1995) 21

Silica
Hydrogen in Glass, Photoinduced Effects 190 (1995) 180

Silicates
Nuclear Magnetic Resonance, Structure 190 (1995) 296

Silicon
Alloys, Conductivity, Hydrogenation, Thin Films 190 (1995) 107
Annealing Effects, Hydrogenation, Photoinduced Effects, Thermal Properties 190 (1995) 157
Electronic Conductivity, Hydrogen Effects 190 (1995) 117

Small Angle X-ray Scattering
Amorphous Carbon, Secondary Electron Emission 190 (1995) 276

Sol–Gel Processes
Diffusion, Gels 190 (1995) 206
Nuclear Magnetic Resonance, Oxides 190 (1995) 212

Stäbler–Wronski Effect
Relaxation, Structure 190 (1995) 151

Structural Relaxation
Aerogels, Processing Variables 190 (1995) 264
Defects, Transient Effects 190 (1995) 142

Structure
Glass Ceramics, Porosity 190 (1995) 185
Infra-red Absorption, Phosphates 190 (1995) 288
Nuclear Magnetic Resonance, Silicates 190 (1995) 296
Relaxation, Stäbler–Wronski Effect 190 (1995) 151

Theory
Hopping 190 (1995) 112

Thermal Properties
Annealing Effects, Hydrogenation, Photoinduced Effects, Silicon 190 (1995) 157
Halide Glasses, Oxides 190 (1995) 251
Polymers, Raman Spectra, Tunneling 190 (1995) 258

Thin Films
Alloys, Conductivity, Hydrogenation, Silicon 190 (1995) 107
Annealing Effects, Defects, Hydrogenation 190 (1995) 163

Transient Effects
Defects, Photoconductivity, Relaxation 190 (1995) 123
Defects, Structural Relaxation 190 (1995) 142

Transport Properties – Solids
Amorphous Semiconductors, Electronic Structure, Modelling 190 (1995) 283

Tunneling
Polymers, Raman Spectra, Thermal Properties 190 (1995) 258